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ST-NXP Wireless



ISP1105/1106

Advanced Universal Serial Bus transceivers

Rev. 08 — 19 February 2004

Product data

1. General description

The ISP1105/1106 range of Universal Serial Bus (USB) transceivers are compliant with the *Universal Serial Bus Specification Rev. 2.0*. They can transmit and receive serial data at both full-speed (12 Mbit/s) and low-speed (1.5 Mbit/s) data rates. The ISP1105/1106 range can be used as a USB device transceiver or a USB host transceiver.

They allow USB Application Specific ICs (ASICs) and Programmable Logic Devices (PLDs) with power supply voltages from 1.65 V to 3.6 V to interface with the physical layer of the Universal Serial Bus. They have an integrated 5 V-to-3.3 V voltage regulator for direct powering via the USB supply V_{BUS} .

ISP1105 allows single-ended and differential input modes selectable by a MODE input and it is available in HVQFN16 and HBCC16 packages. ISP1106 allows only differential input mode and is available in both TSSOP16 and HBCC16 packages.

The ISP1105/1106 are ideal for portable electronics devices such as mobile phones, digital still cameras, Personal Digital Assistants (PDA) and Information Appliances (IA).

2. Features

- Complies with *Universal Serial Bus Specification Rev. 2.0*
- Can transmit and receive serial data at both full-speed (12 Mbit/s) and low-speed (1.5 Mbit/s) data rates
- Integrated bypassable 5 V-to-3.3 V voltage regulator for powering via USB V_{BUS}
- V_{BUS} disconnection indication through VP and VM
- Used as a USB device transceiver or a USB host transceiver
- Stable RCV output during SE0 condition
- Two single-ended receivers with hysteresis
- Low-power operation
- Supports an I/O voltage range from 1.65 V to 3.6 V
- ± 12 kV ESD protection at the D+, D-, $V_{CC(5.0)}$ and GND pins
- Full industrial operating temperature range from -40 to $+85$ °C
- Available in small HBCC16, HVQFN16 (only ISP1105) and TSSOP16 (only ISP1106) packages; HBCC16 and HVQFN16 are lead-free and halogen-free packages.



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3. Applications

- Portable electronic devices, such as:
 - ◆ Mobile phone
 - ◆ Digital still camera
 - ◆ Personal Digital Assistant (PDA)
 - ◆ Information Appliance (IA).

4. Ordering information

Table 1: Ordering information

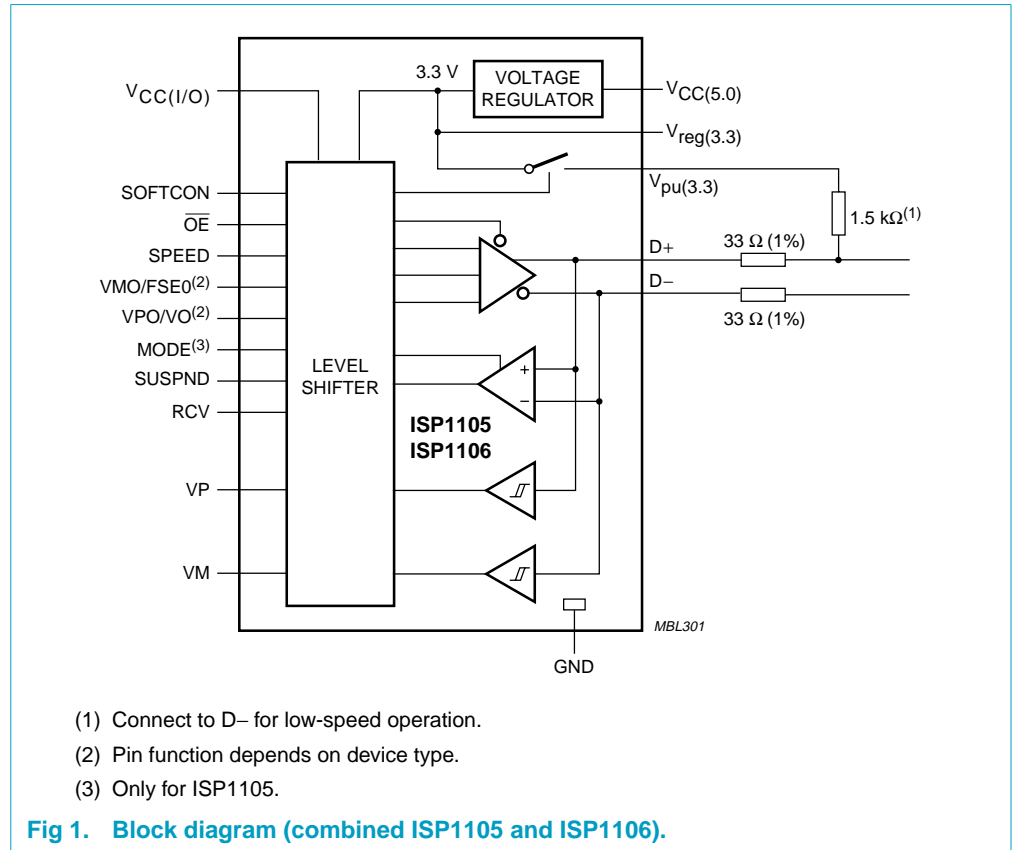
Type number	Package		
	Name	Description	Version
ISP1105BS	HVQFN16	plastic thermal enhanced very thin quad flat package; no leads; 16 terminals; body 3 × 3 × 0.85 mm	SOT758-1
ISP1105W	HBCC16	plastic thermal enhanced bottom chip carrier; 16 terminals; body 3 × 3 × 0.65 mm	SOT639-2
ISP1106DH	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
ISP1106W	HBCC16	plastic thermal enhanced bottom chip carrier; 16 terminals; body 3 × 3 × 0.65 mm	SOT639-2

4.1 Ordering options

Table 2: Selection guide

Product	Package	Description
ISP1105	HVQFN16 and HBCC16	supports both single-ended and differential input modes; see Table 5 and Table 6 .
ISP1106	TSSOP16 and HBCC16	supports only the differential input mode; see Table 6 .

5. Block diagram



6. Pinning information

6.1 Pinning

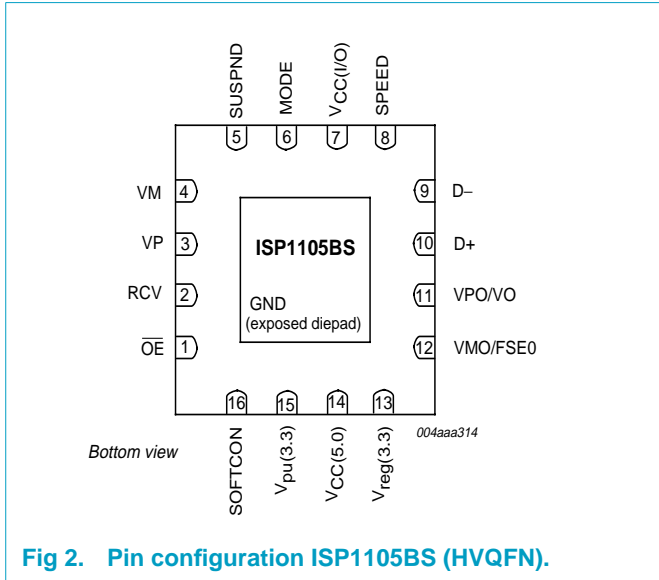


Fig 2. Pin configuration ISP1105BS (HVQFN).

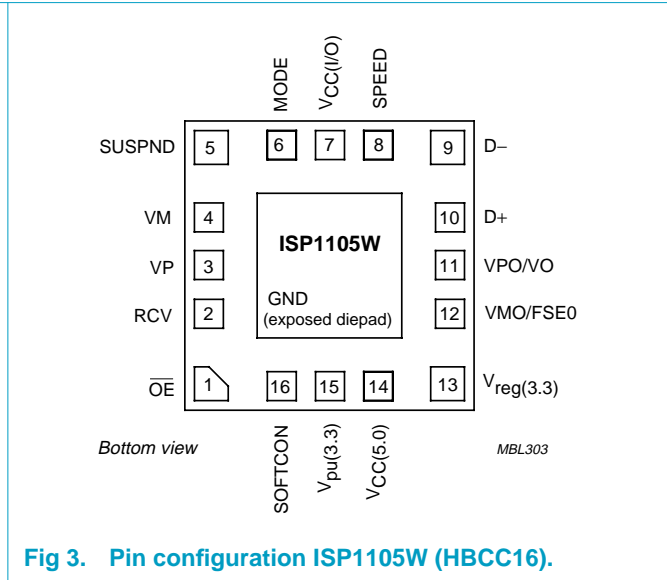


Fig 3. Pin configuration ISP1105W (HBCC16).

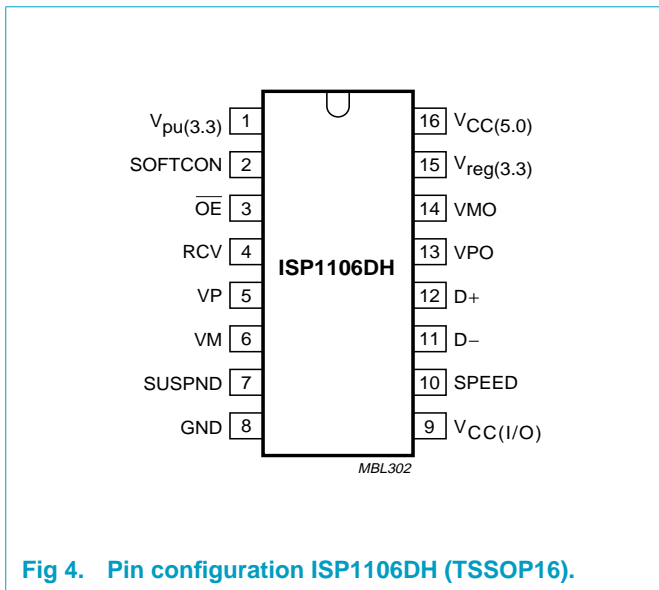


Fig 4. Pin configuration ISP1106DH (TSSOP16).

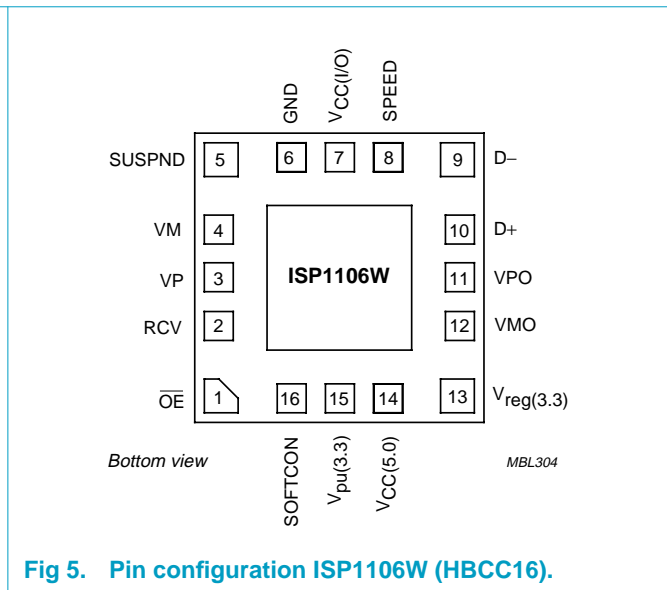


Fig 5. Pin configuration ISP1106W (HBCC16).

6.2 Pin description

Table 3: Pin description

Symbol ^[1]	Pin				Type	Description
	ISP1105		ISP1106			
	BS	W	DH	W		
OE	1	1	3	1	I	output enable input (CMOS level with respect to $V_{CC(I/O)}$, active LOW); enables the transceiver to transmit data on the USB bus input pad; push pull; CMOS
RCV	2	2	4	2	O	differential data receiver output (CMOS level with respect to $V_{CC(I/O)}$); driven LOW when input SUSPND is HIGH; the output state of RCV is preserved and stable during an SE0 condition output pad; push pull; 4 mA output drive; CMOS
VP	3	3	5	3	O	single-ended D+ receiver output (CMOS level with respect to $V_{CC(I/O)}$); for external detection of single-ended zero (SE0), error conditions, speed of connected device; driven HIGH when no supply voltage is connected to $V_{CC(5.0)}$ and $V_{reg(3.3)}$ output pad; push pull; 4 mA output drive; CMOS
VM	4	4	6	4	O	single-ended D- receiver output (CMOS level with respect to $V_{CC(I/O)}$); for external detection of single-ended zero (SE0), error conditions, speed of connected device; driven HIGH when no supply voltage is connected to $V_{CC(5.0)}$ and $V_{reg(3.3)}$ output pad; push pull; 4 mA output drive; CMOS
SUSPND	5	5	7	5	I	suspend input (CMOS level with respect to $V_{CC(I/O)}$); a HIGH level enables low-power state while the USB bus is inactive and drives output RCV to a LOW level input pad; push pull; CMOS
MODE	6	6	-	-	I	mode input (CMOS level with respect to $V_{CC(I/O)}$); a HIGH level enables the differential input mode (VPO, VMO) whereas a LOW level enables a single-ended input mode (VO, FSE0); see Table 5 and Table 6 input pad; push pull; CMOS
GND	die pad	die pad	8	6	-	ground supply ^[2]
$V_{CC(I/O)}$	7	7	9	7	-	supply voltage for digital I/O pins (1.65 to 3.6 V). When $V_{CC(I/O)}$ is not connected, the (D+, D-) pins are in three-state; this supply pin is totally independent of $V_{CC(5.0)}$ and $V_{reg(3.3)}$ and must never exceed the $V_{reg(3.3)}$ voltage
SPEED	8	8	10	8	I	speed selection input (CMOS level with respect to $V_{CC(I/O)}$); adjusts the slew rate of differential data outputs D+ and D- according to the transmission speed LOW — low-speed (1.5 Mbit/s) HIGH — full-speed (12 Mbit/s) input pad; push pull; CMOS
D-	9	9	11	9	AI/O	negative USB data bus connection (analog, differential); for low-speed mode connect to pin $V_{pu(3.3)}$ via a 1.5 kΩ resistor
D+	10	10	12	10	AI/O	positive USB data bus connection (analog, differential); for full-speed mode connect to pin $V_{pu(3.3)}$ via a 1.5 kΩ resistor

Table 3: Pin description...continued

Symbol ^[1]	Pin				Type	Description
	ISP1105		ISP1106			
	BS	W	DH	W		
VPO/VO	11	11	-	-	I	driver data input (CMOS level with respect to $V_{CC(I/O)}$, Schmitt trigger); see Table 5 and Table 6
VPO	-	-	13	11		input pad; push pull; CMOS
VO	-	-	-	-		
VMO/FSE0	12	12	-	-	I	driver data input (CMOS level with respect to $V_{CC(I/O)}$, Schmitt trigger); see Table 5 and Table 6
VMO	-	-	14	12		input pad; push pull; CMOS
FSE0	-	-	-	-		
$V_{reg(3.3)}$	13	13	15	13	-	internal regulator option: regulated supply voltage output (3.0 to 3.6 V) during 5 V operation; a decoupling capacitor of at least 0.1 μ F is required regulator bypass option: used as a supply voltage input for 3.3 V \pm 10% operation
$V_{CC(5.0)}$	14	14	16	14	-	internal regulator option: supply voltage input (4.0 to 5.5 V); can be connected directly to USB supply V_{BUS} regulator bypass option: connect to $V_{reg(3.3)}$
$V_{pu(3.3)}$	15	15	1	15	-	pull-up supply voltage (3.3 V \pm 10%); connect an external 1.5 k Ω resistor on D+ (full-speed) or D- (low-speed); pin function is controlled by input SOFTCON SOFTCON = LOW — $V_{pu(3.3)}$ floating (high impedance); ensures zero pull-up current SOFTCON = HIGH — $V_{pu(3.3)} = 3.3$ V; internally connected to $V_{reg(3.3)}$
SOFTCON	16	16	2	16	I	software controlled USB connection input; a HIGH level applies 3.3 V to pin $V_{pu(3.3)}$, which is connected to an external 1.5 k Ω pull-up resistor; this allows USB connect/disconnect signalling to be controlled by software input pad; push pull; CMOS

[1] Symbol names with an overscore (e.g. \overline{NAME}) indicate active LOW signals.

[2] ISP1105: ground terminal is connected to the exposed die pad (heatsink).

7. Functional description

7.1 Function selection

Table 4: Function table

SUSPND	\overline{OE}	(D+, D-)	RCV	VP/VM	Function
L	L	driving and receiving	active	active	normal driving (differential receiver active)
L	H	receiving ^[1]	active	active	receiving
H	L	driving	inactive ^[2]	active	driving during 'suspend' ^[3] (differential receiver inactive)
H	H	high-Z ^[1]	inactive ^[2]	active	low-power state

- [1] Signal levels on (D+, D-) are determined by other USB devices and external pull-up/down resistors.
- [2] In 'suspend' mode (SUSPND = HIGH) the differential receiver is inactive and output RCV is always LOW. Out-of-suspend ('K') signalling is detected via the single-ended receivers VP and VM.
- [3] During suspend, the slew-rate control circuit of low-speed operation is disabled. The (D+, D-) lines are still driven to their intended states, without slew-rate control. This is permitted because driving during suspend is used to signal remote wake-up by driving a 'K' signal (one transition from idle to 'K' state) for a period of 1 to 15 ms.

7.2 Operating functions

Table 5: Driving function (pin $\overline{OE} = L$) using single-ended input data interface for ISP1105 (pin MODE = L)

FSE0	VO	Data
L	L	differential logic 0
L	H	differential logic 1
H	L	SE0
H	H	SE0

Table 6: Driving function (pin $\overline{OE} = L$) using differential input data interface for ISP1105 (pin MODE = H) and ISP1106

VMO	VPO	Data
L	L	SE0
L	H	differential logic 1
H	L	differential logic 0
H	H	illegal state

Table 7: Receiving function (pin $\overline{OE} = H$)

(D+, D-)	RCV	VP ^[1]	VM ^[1]
Differential logic 0	L	L	H
Differential logic 1	H	H	L
SE0	RCV* ^[2]	L	L

- [1] VP = VM = H indicates the sharing mode ($V_{CC(5.0)}$ and $V_{reg(3.3)}$ are disconnected).
- [2] RCV* denotes the signal level on output RCV just before SE0 state occurs. This level is stable during the SE0 period.

7.3 Power supply configurations

The ISP1105/1106 can be used with different power supply configurations, which can be changed dynamically. An overview is given in [Table 9](#).

Normal mode — Both $V_{CC(I/O)}$ and $V_{CC(5.0)}$ or ($V_{CC(5.0)}$ and $V_{reg(3.3)}$) are connected. For 5 V operation, $V_{CC(5.0)}$ is connected to a 5 V source (4.0 to 5.5 V). The internal voltage regulator then produces 3.3 V for the USB connections. For 3.3 V operation, both $V_{CC(5.0)}$ and $V_{reg(3.3)}$ are connected to a 3.3 V source (3.0 to 3.6 V). $V_{CC(I/O)}$ is independently connected to a voltage source (1.65 V to 3.6 V), depending on the supply voltage of the external circuit.

Disable mode — $V_{CC(I/O)}$ is not connected, $V_{CC(5.0)}$ or ($V_{CC(5.0)}$ and $V_{reg(3.3)}$) are connected. In this mode, the internal circuits of the ISP1105/1106 ensure that the (D+, D-) pins are in three-state and the power consumption drops to the low-power (suspended) state level. Some hysteresis is built into the detection of $V_{CC(I/O)}$ lost.

Sharing mode — $V_{CC(I/O)}$ is connected, ($V_{CC(5.0)}$ and $V_{reg(3.3)}$) are not connected. In this mode, the (D+, D-) pins are made three-state and the ISP1105/1106 allows external signals of up to 3.6 V to share the (D+, D-) lines. The internal circuits of the ISP1105/1106 ensure that virtually no current (maximum 10 μ A) is drawn via the (D+, D-) lines. The power consumption through pin $V_{CC(I/O)}$ drops to the low-power (suspended) state level. Both the VP and VM pins are driven HIGH to indicate this mode. Pin RCV is made LOW. Some hysteresis is built into the detection of $V_{reg(3.3)}$ lost.

Table 8: Pin states in disable or sharing mode

Pins	Disable mode state	Sharing mode state
$V_{CC(5.0)} / V_{reg(3.3)}$	5 V input / 3.3 V output; 3.3 V input / 3.3 V input	not present
$V_{CC(I/O)}$	not present	1.65 V to 3.6 V input
$V_{pu(3.3)}$	high impedance (off)	high impedance (off)
(D+, D-)	high impedance	high impedance
(VP, VM)	invalid ^[1]	H
RCV	invalid ^[1]	L
Inputs (VO/VPO, FSE0/VMO, SPEED, MODE ^[2] , SUSPND, \overline{OE} , SOFTCON)	high impedance	high impedance

[1] High impedance or driven LOW.

[2] ISP1105 only.

Table 9: Power supply configuration overview

$V_{CC(5.0)}$ or $V_{reg(3.3)}$	$V_{CC(I/O)}$	Configuration	Special characteristics
Connected	connected	normal mode	-
Connected	not connected	disable mode	(D+, D-) and $V_{pu(3.3)}$ high impedance; VP, VM, RCV: invalid ^[1]
Not connected	connected	sharing mode	(D+, D-) and $V_{pu(3.3)}$ high impedance; VP, VM driven HIGH; RCV driven LOW

[1] High impedance or driven LOW.

7.4 Power supply input options

The ISP1105/1106 range has two power supply input options.

Internal regulator — $V_{CC(5.0)}$ is connected to 4.0 to 5.5 V. The internal regulator is used to supply the internal circuitry with 3.3 V (nominal). The $V_{reg(3.3)}$ pin becomes a 3.3 V output reference.

Regulator bypass — $V_{CC(5.0)}$ and $V_{reg(3.3)}$ are connected to the same supply. The internal regulator is bypassed and the internal circuitry is supplied directly from the $V_{reg(3.3)}$ power supply. The voltage range is 3.0 to 3.6 V to comply with the USB specification.

The supply voltage range for each input option is specified in [Table 10](#).

Table 10: Power supply input options

Input option	$V_{CC(5.0)}$	$V_{reg(3.3)}$	$V_{CC(I/O)}$
Internal regulator	supply input for internal regulator (4.0 to 5.5 V)	voltage reference output (3.3 V, 300 μ A)	supply input for digital I/O pins (1.65 V to 3.6 V)
Regulator bypass	connected to $V_{reg(3.3)}$ with maximum voltage drop of 0.3 V (2.7 to 3.6 V)	supply input (3.0 V to 3.6 V)	supply input for digital I/O pins (1.65 V to 3.6 V)

8. Electrostatic discharge (ESD)

8.1 ESD protection

The pins that are connected to the USB connector (D+, D-, $V_{CC(5.0)}$ and GND) have a minimum of ± 12 kV ESD protection. The ± 12 kV measurement is limited by the test equipment. Capacitors of $4.7 \mu\text{F}$ connected from $V_{reg(3.3)}$ to GND and $V_{CC(5.0)}$ to GND are required to achieve this ± 12 kV ESD protection (see Figure 6).

ISP1105/1106 can withstand ± 12 kV using the Human Body Model and ± 5 kV using the Contact Discharge Method as specified in IEC 61000-4-2.

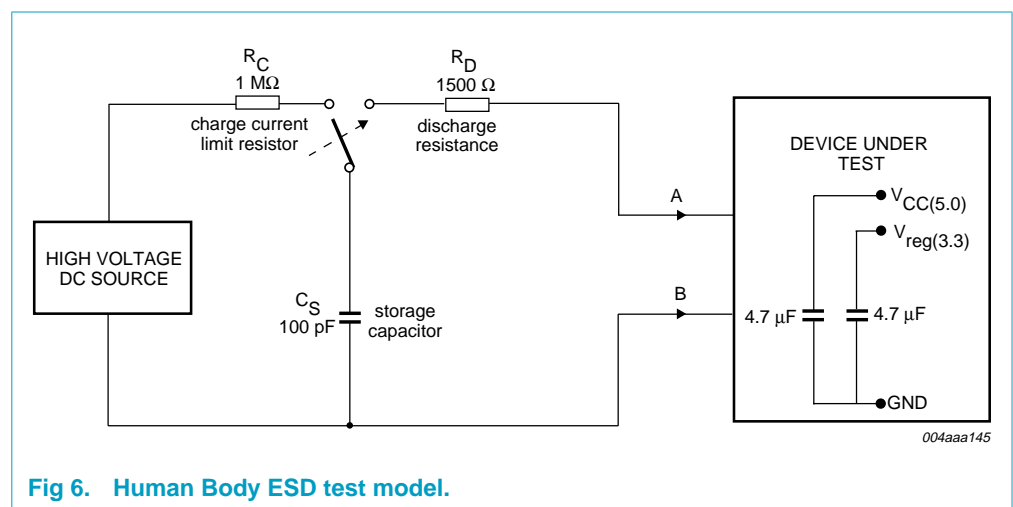


Fig 6. Human Body ESD test model.

8.2 ESD test conditions

A detailed report on test set-up and results is available on request.

9. Limiting values

Table 11: Absolute maximum ratings

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(5.0)}$	supply voltage		-0.5	+6.0	V
$V_{CC(I/O)}$	I/O supply voltage		-0.5	+4.6	V
$V_{reg(3.3)}$	regulated supply voltage		-0.5	+4.6	V
V_I	DC input voltage		-0.5	$V_{CC(I/O)} + 0.5$	V
I_{lu}	latch-up current	$V_I = -1.8$ to 5.4 V	-	100	mA
V_{esd}	electrostatic discharge voltage	$I_{LI} < 1 \mu\text{A}$	[1][2]		
		on pins D+, D-, $V_{CC(5.0)}$ and GND	-12000	+12000	V
		on other pins	-2000	+2000	V
T_{stg}	storage temperature		-40	+125	°C

[1] Testing equipment limits measurement to only ± 12 kV. Capacitors needed on $V_{CC(5.0)}$ and $V_{reg(3.3)}$; see Section 8.

[2] Equivalent to discharging a 100 pF capacitor via a 1.5 k Ω resistor (Human Body Model).

10. Recommended operating conditions

Table 12: Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CC(5.0)}$	supply voltage (internal regulator option)	5 V operation	4.0	5.0	5.5	V
$V_{reg(3.3)}$	supply voltage (regulator bypass option)	3.3 V operation	3.0	3.3	3.6	V
$V_{CC(I/O)}$	I/O supply voltage		1.65	-	3.6	V
V_I	input voltage		0	-	$V_{CC(I/O)}$	V
$V_{I(AI/O)}$	input voltage on analog I/O pins (D+/D-)		0	-	3.6	V
T_{amb}	operating ambient temperature		-40	-	+85	°C

11. Static characteristics

Table 13: Static characteristics: supply pins

$V_{CC} = 4.0$ to 5.5 V or $V_{reg(3.3)} = 3.0$ to 3.6 V; $V_{CC(I/O)} = 1.65$ to 3.6 V; $V_{GND} = 0$ V; see [Table 10](#) for valid voltage level combinations; $T_{amb} = -40$ to $+85$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{reg(3.3)}$	regulated supply voltage output	internal regulator option; $I_{load} \leq 300$ μ A	[1][2] 3.0	3.3	3.6	V
I_{CC}	operating supply current	full-speed transmitting and receiving at 12 Mbit/s; $C_L = 50$ pF on D+/D-	[3] -	4	8	mA
$I_{CC(I/O)}$	operating I/O supply current	full-speed transmitting and receiving at 12 Mbit/s	[3] -	1	2	mA
$I_{CC(idle)}$	supply current during full-speed idle and SE0	full-speed idle: $V_{D+} > 2.7$ V, $V_{D-} < 0.3$ V; SE0: $V_{D+} < 0.3$ V, $V_{D-} < 0.3$ V	[4] -	-	500	μ A
$I_{CC(I/O)(static)}$	static I/O supply current	full-speed idle, SE0 or suspend	-	-	20	μ A
$I_{CC(susp)}$	suspend supply current	SUSPND = HIGH	[4] -	-	20	μ A
$I_{CC(dis)}$	disable mode supply current	$V_{CC(I/O)}$ not connected	[4] -	-	20	μ A
$I_{CC(I/O)(sharing)}$	sharing mode I/O supply current	$V_{CC(5.0)}$ or $V_{reg(3.3)}$ not connected	-	-	20	μ A
$I_{Dx(sharing)}$	sharing mode load current on pins D+ and D-	$V_{CC(5.0)}$ or $V_{reg(3.3)}$ not connected; SOFTCON = LOW; $V_{Dx} = 3.6$ V	-	-	10	μ A
$V_{reg(3.3)th}$	regulated supply voltage detection threshold	1.65 V $\leq V_{CC(I/O)} \leq V_{reg(3.3)}$; 2.7 V $\leq V_{reg(3.3)} \leq 3.6$ V	-	-	0.8	V
		supply lost	-	-	-	V
		supply present	[5] 2.4	-	-	V
$V_{reg(3.3)hys}$	regulated supply voltage detection hysteresis	$V_{CC(I/O)} = 1.8$ V	-	0.45	-	V
$V_{CC(I/O)th}$	I/O supply voltage detection threshold	$V_{reg(3.3)} = 2.7$ to 3.6 V	-	-	0.5	V
		supply lost	-	-	-	V
		supply present	1.4	-	-	V
$V_{CC(I/O)hys}$	I/O supply voltage detection hysteresis	$V_{reg(3.3)} = 3.3$ V	-	0.45	-	V

[1] I_{load} includes the pull-up resistor current via pin $V_{pu(3.3)}$.

[2] In 'suspend' mode, the minimum voltage is 2.7 V.

[3] Maximum value is characterized only, not tested in production.

[4] Excluding any load current and $V_{pu(3.3)}/V_{sw}$ source current to the 1.5 k Ω and 15 k Ω pull-up and pull-down resistors (200 μ A typ.).

[5] When $V_{CC(I/O)} < 2.7$ V, the minimum value for $V_{th(reg3.3)(present)}$ is 2.0 V.

Table 14: Static characteristics: digital pins

$V_{CC(I/O)} = 1.65$ to 3.6 V; $V_{GND} = 0$ V; $T_{amb} = -40$ to $+85$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CC(I/O)} = 1.65$ to 3.6 V						
Input levels						
V_{IL}	LOW-level input voltage		-	-	$0.3V_{CC(I/O)}$	V
V_{IH}	HIGH-level input voltage		$0.6V_{CC(I/O)}$	-	-	V
Output levels						
V_{OL}	LOW-level output voltage	$I_{OL} = 100 \mu A$	-	-	0.15	V
		$I_{OL} = 2$ mA	-	-	0.4	V
V_{OH}	HIGH-level output voltage	$I_{OH} = 100 \mu A$	$V_{CC(I/O)} - 0.15$	-	-	V
		$I_{OH} = 2$ mA	$V_{CC(I/O)} - 0.4$	-	-	V
Leakage current						
I_{LI}	input leakage current		-1	-	+1	μA
Example 1: $V_{CC(I/O)} = 1.8$ V \pm 0.15 V						
Input levels						
V_{IL}	LOW-level input voltage		-	-	0.5	V
V_{IH}	HIGH-level input voltage		1.2	-	-	V
Output levels						
V_{OL}	LOW-level output voltage	$I_{OL} = 100 \mu A$	-	-	0.15	V
		$I_{OL} = 2$ mA	-	-	0.4	V
V_{OH}	HIGH-level output voltage	$I_{OH} = 100 \mu A$	1.5	-	-	V
		$I_{OH} = 2$ mA	1.25	-	-	V
Example 2: $V_{CC(I/O)} = 2.5$ V \pm 0.2 V						
Input levels						
V_{IL}	LOW-level input voltage		-	-	0.7	V
V_{IH}	HIGH-level input voltage		1.7	-	-	V
Output levels						
V_{OL}	LOW-level output voltage	$I_{OL} = 100 \mu A$	-	-	0.15	V
		$I_{OL} = 2$ mA	-	-	0.4	V
V_{OH}	HIGH-level output voltage	$I_{OH} = 100 \mu A$	2.15	-	-	V
		$I_{OH} = 2$ mA	1.9	-	-	V
Example 3: $V_{CC(I/O)} = 3.3$ V \pm 0.3 V						
Input levels						
V_{IL}	LOW-level input voltage		-	-	0.9	V
V_{IH}	HIGH-level input voltage		2.15	-	-	V
Output levels						
V_{OL}	LOW-level output voltage	$I_{OL} = 100 \mu A$	-	-	0.15	V
		$I_{OL} = 2$ mA	-	-	0.4	V
V_{OH}	HIGH-level output voltage	$I_{OH} = 100 \mu A$	2.85	-	-	V
		$I_{OH} = 2$ mA	2.6	-	-	V
Capacitance						
C_{IN}	input capacitance	pin to GND	-	-	10	pF

Table 15: Static characteristics: analog I/O pins (D+, D-)

$V_{CC} = 4.0$ to 5.5 V or $V_{reg(3.3)} = 3.0$ to 3.6 V; $V_{GND} = 0$ V; $T_{amb} = -40$ to $+85$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Input levels						
Differential receiver						
V_{DI}	differential input sensitivity	$ V_{I(D+)} - V_{I(D-)} $	0.2	-	-	V
V_{CM}	differential common mode voltage	includes V_{DI} range	0.8	-	2.5	V
Single-ended receiver						
V_{IL}	LOW-level input voltage		-	-	0.8	V
V_{IH}	HIGH-level input voltage		2.0	-	-	V
V_{hys}	hysteresis voltage		0.4	-	0.7	V
Output levels						
V_{OL}	LOW-level output voltage	$R_L = 1.5$ k Ω to +3.6 V	-	-	0.3	V
V_{OH}	HIGH-level output voltage	$R_L = 15$ k Ω to GND	[1] 2.8	-	3.6	V
Leakage current						
I_{LZ}	OFF-state leakage current		-1	-	+1	μ A
Capacitance						
C_{IN}	transceiver capacitance	pin to GND	-	-	20	pF
Resistance						
Z_{DRV}	driver output impedance	steady-state drive	[2] 34	39	44	Ω
Z_{INP}	input impedance		10	-	-	M Ω
R_{SW}	internal switch resistance at pin $V_{pu(3.3)}$		-	-	10	Ω
Termination						
V_{TERM}	termination voltage for upstream port pull-up (R_{PU})		[3][4] 3.0	-	3.6	V

[1] $V_{OH(min)} = V_{reg(3.3)} - 0.2$ V.

[2] Includes external resistors of 33 $\Omega \pm 1\%$ on both D+ and D-.

[3] This voltage is available at pins $V_{reg(3.3)}$ and $V_{pu(3.3)}$.

[4] In 'suspend' mode the minimum voltage is 2.7 V.

12. Dynamic characteristics

Table 16: Dynamic characteristics: analog I/O pins (D+, D-)^[1]

$V_{CC} = 4.0$ to 5.5 V or $V_{reg(3.3)} = 3.0$ to 3.6 V; $V_{CC(I/O)} = 1.65$ to 3.6 V; $V_{GND} = 0$ V; see [Table 10](#) for valid voltage level combinations; $T_{amb} = -40$ to $+85$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Driver characteristics						
Full-speed mode						
t_{FR}	rise time	$C_L = 50$ to 125 pF; 10% to 90% of $ V_{OH} - V_{OL} $; see Figure 7	4	-	20	ns
t_{FF}	fall time	$C_L = 50$ to 125 pF; 90% to 10% of $ V_{OH} - V_{OL} $; see Figure 7	4	-	20	ns
FRFM	differential rise/fall time matching (t_{FR}/t_{FF})	excluding the first transition from idle state	90	-	111.1	%
V_{CRS}	output signal crossover voltage	excluding the first transition from idle state; see Figure 10	^[2] 1.3	-	2.0	V
Low-speed mode						
t_{LR}	rise time	$C_L = 50$ to 600 pF; 10% to 90% of $ V_{OH} - V_{OL} $; see Figure 7	75	-	300	ns
t_{LF}	fall time	$C_L = 50$ to 600 pF; 90% to 10% of $ V_{OH} - V_{OL} $; see Figure 7	75	-	300	ns
LRFM	differential rise/fall time matching (t_{LR}/t_{LF})	excluding the first transition from idle state	80	-	125	%
V_{CRS}	output signal crossover voltage	excluding the first transition from idle state; see Figure 10	^[2] 1.3	-	2.0	V
Driver timing						
Full-speed mode						
$t_{PLH(dr)}$	driver propagation delay (VO/VPO, FSE0/VMO to D+,D-)	LOW-to-HIGH; see Figure 10	-	-	18	ns
$t_{PHL(dr)}$	driver propagation delay (VO/VPO, FSE0/VMO to D+,D-)	HIGH-to-LOW; see Figure 10	-	-	18	ns
t_{PHZ}	driver disable delay (\overline{OE} to D+,D-)	HIGH-to-OFF; see Figure 8	-	-	15	ns
t_{PLZ}	driver disable delay (\overline{OE} to D+,D-)	LOW-to-OFF; see Figure 8	-	-	15	ns
t_{PZH}	driver enable delay (\overline{OE} to D+,D-)	OFF-to-HIGH; see Figure 8	-	-	15	ns
t_{PZL}	driver enable delay (\overline{OE} to D+,D-)	OFF-to-LOW; see Figure 8	-	-	15	ns
Low-speed mode						

Not specified: low-speed delay timings are dominated by the slow rise/fall times t_{LR} and t_{LF} .

Table 16: Dynamic characteristics: analog I/O pins (D+, D-)[1]...continued

$V_{CC} = 4.0$ to 5.5 V or $V_{reg(3.3)} = 3.0$ to 3.6 V; $V_{CC(I/O)} = 1.65$ to 3.6 V; $V_{GND} = 0$ V; see [Table 10](#) for valid voltage level combinations; $T_{amb} = -40$ to $+85$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Receiver timings (full-speed and low-speed mode)						
Differential receiver						
$t_{PLH(rcv)}$	propagation delay (D+,D- to RCV)	LOW-to-HIGH; see Figure 9	-	-	15	ns
$t_{PHL(rcv)}$	propagation delay (D+,D- to RCV)	HIGH-to-LOW; see Figure 9	-	-	15	ns
Single-ended receiver						
$t_{PLH(se)}$	propagation delay (D+,D- to VP, VM)	LOW-to-HIGH; see Figure 9	-	-	18	ns
$t_{PHL(se)}$	propagation delay (D+,D- to VP, VM)	HIGH-to-LOW; see Figure 9	-	-	18	ns

- [1] Test circuit: see [Figure 13](#).
- [2] Characterized only, not tested. Limits guaranteed by design.

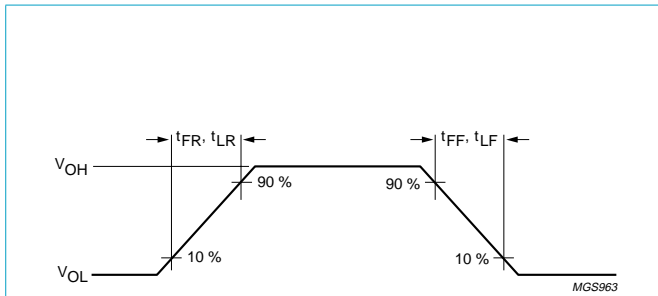


Fig 7. Rise and fall times.

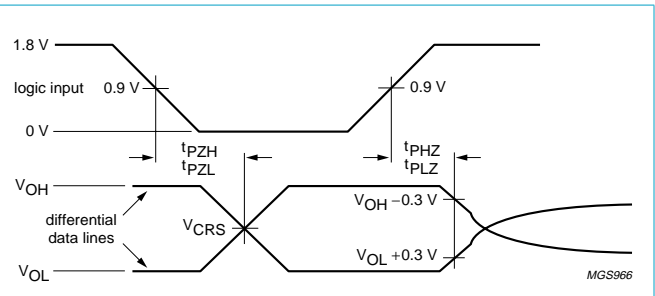


Fig 8. Timing of OE to D+, D-.

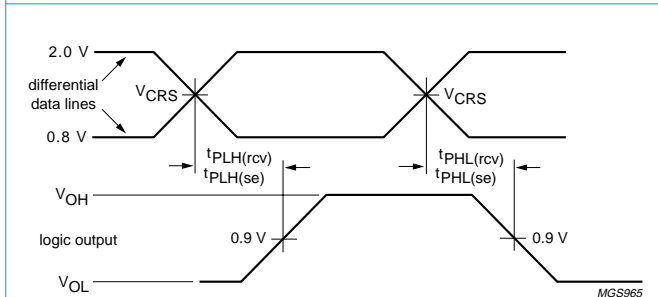


Fig 9. Timing of D+, D- to RCV, VP, VM.

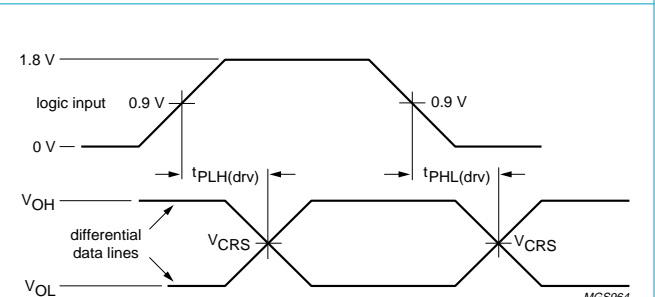
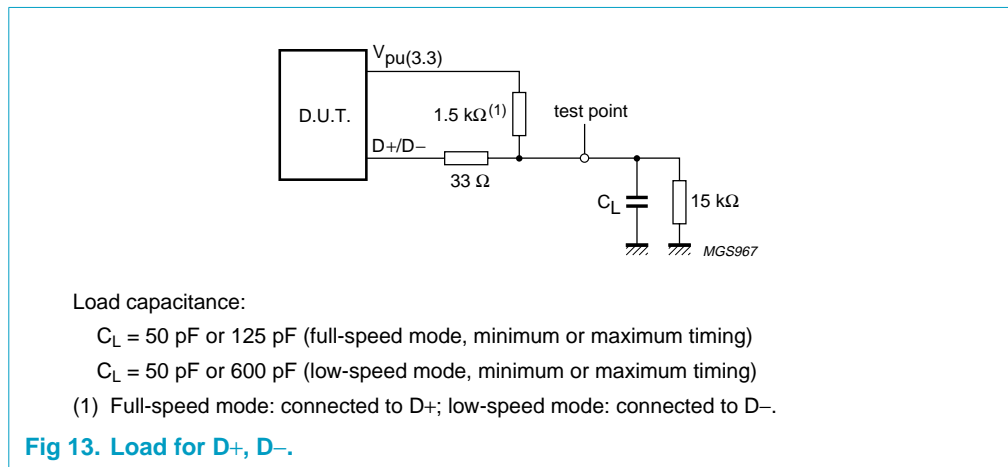
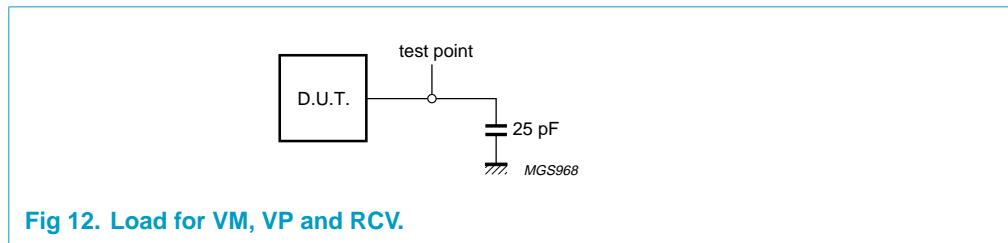
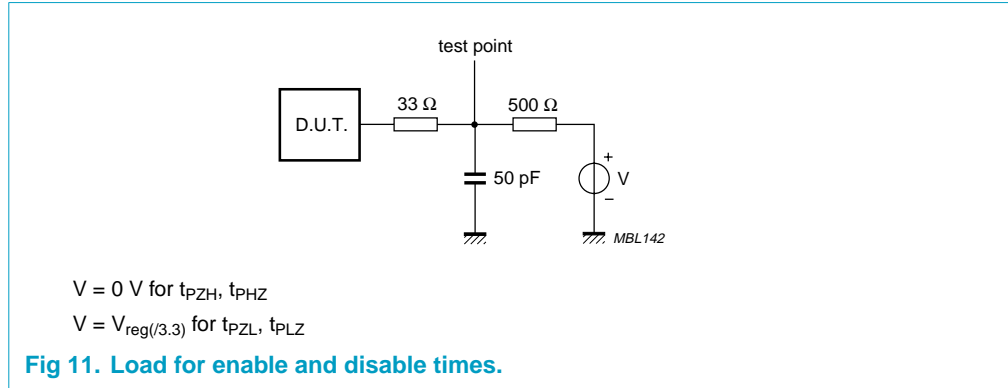


Fig 10. Timing of VO/VPO, FSE0/VMO to D+, D-.

13. Test information



14. Package outline

HBCC16: plastic thermal enhanced bottom chip carrier; 16 terminals; body 3 x 3 x 0.65 mm

SOT639-2

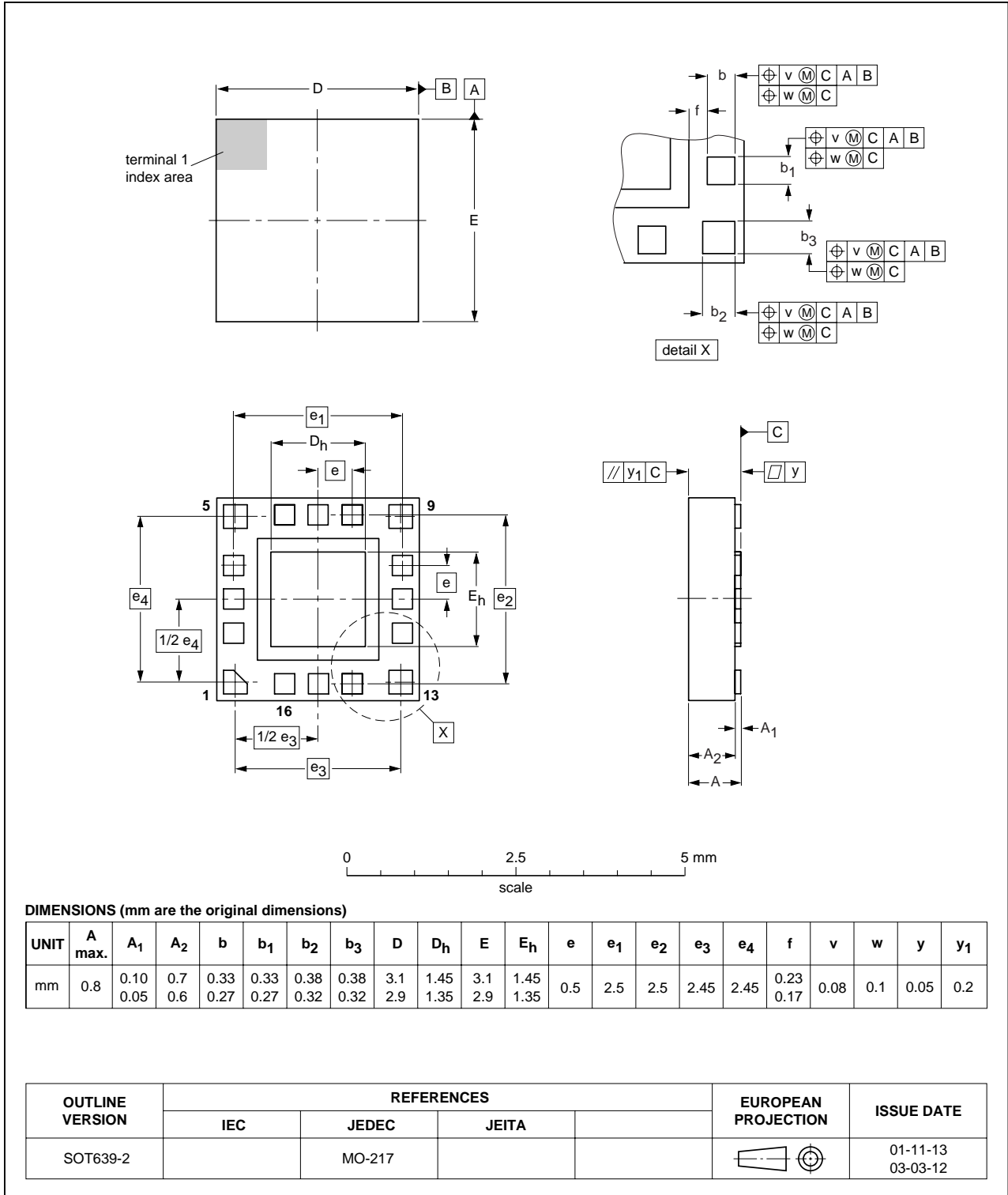


Fig 14. HBCC16 package outline.

HVQFN16: plastic thermal enhanced very thin quad flat package; no leads; 16 terminals; body 3 x 3 x 0.85 mm

SOT758-1

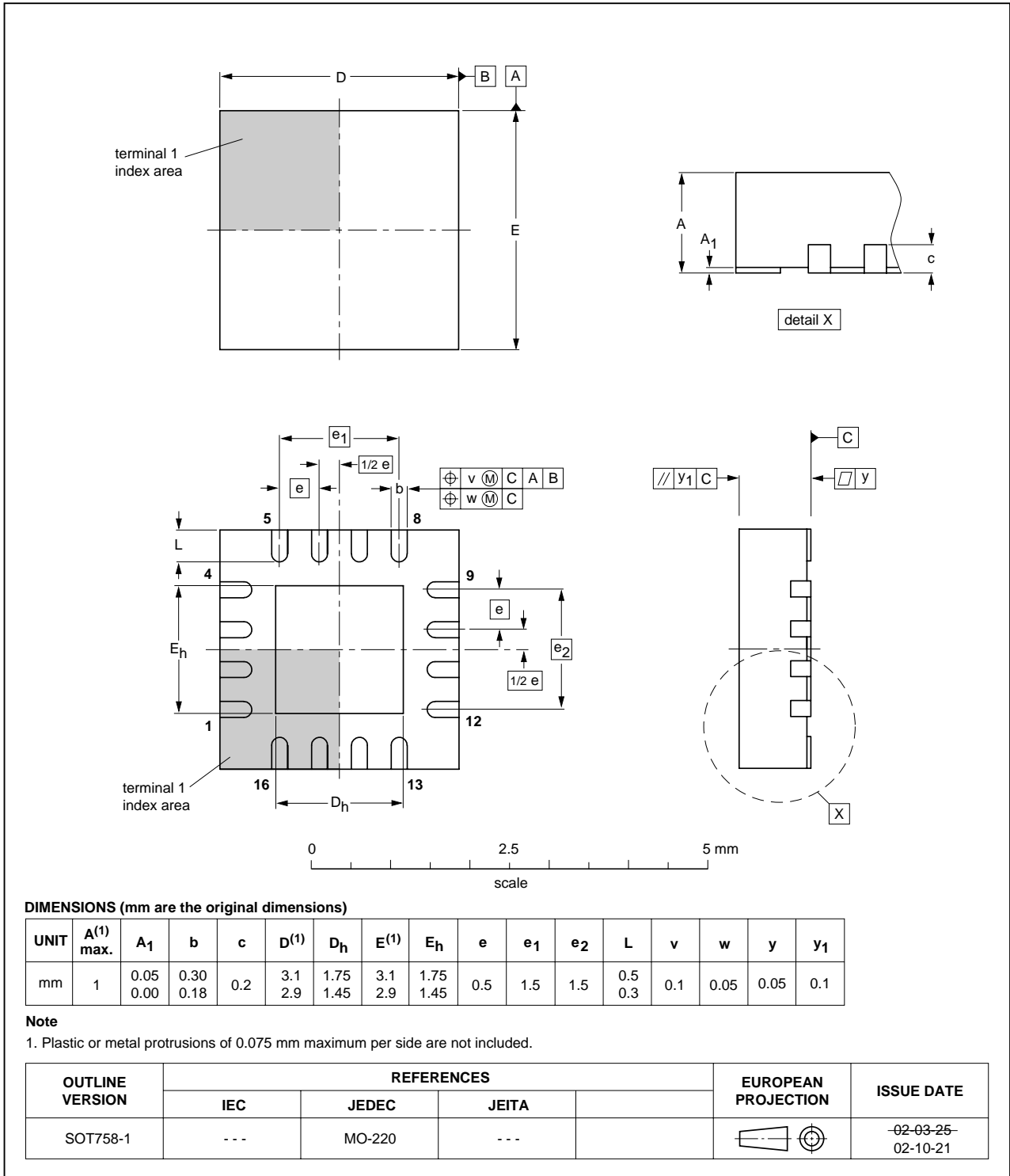


Fig 15. HVQFN16 package outline.

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

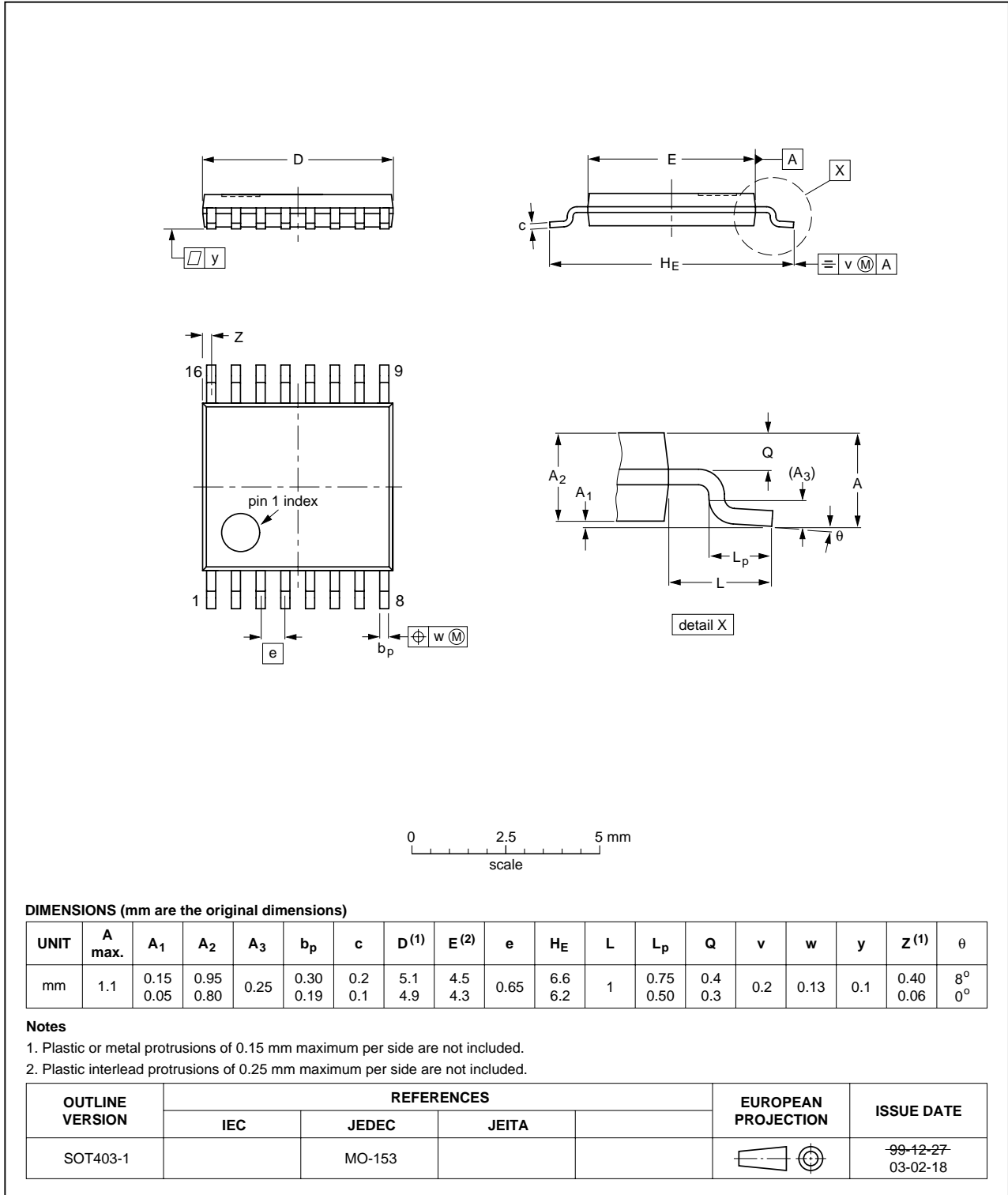


Fig 16. TSSOP16 package outline.

15. Packaging

The ISP1105/1106W (HBCC16 package) is delivered on a type A carrier tape, see Figure 17. The tape dimensions are given in Table 17.

The reel diameter is 330 mm. The reel is made of polystyrene (PS) and is not designed for use in a baking process.

The cumulative tolerance of 10 successive sprocket holes is ± 0.02 mm. The camber must not exceed 1 mm in 100 mm.

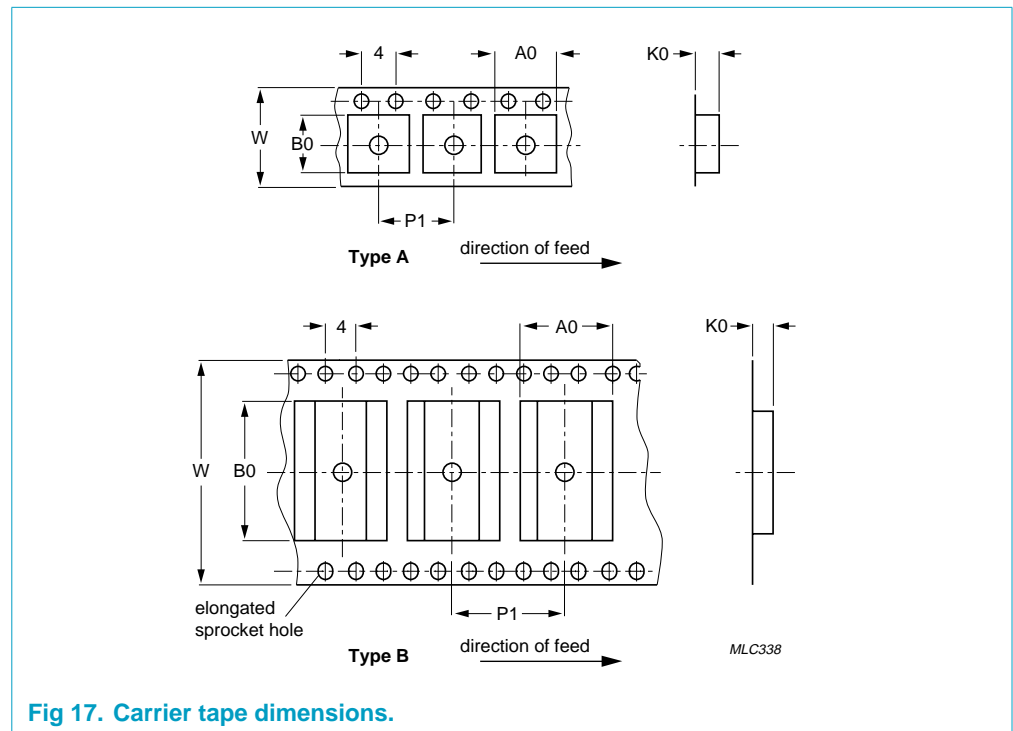


Fig 17. Carrier tape dimensions.

Table 17: Type A carrier tape dimensions for ISP1105/1106W

Dimension	Value	Unit
A ₀	3.3	mm
B ₀	3.3	mm
K ₀	1.1	mm
P ₁	8.0	mm
W	12.0 ±0.3	mm

16. Soldering

16.1 Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *Data Handbook IC26; Integrated Circuit Packages* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended. In these situations reflow soldering is recommended.

16.2 Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement. Driven by legislation and environmental forces the worldwide use of lead-free solder pastes is increasing.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 270 °C depending on solder paste material. The top-surface temperature of the packages should preferably be kept:

- below 225 °C (SnPb process) or below 245 °C (Pb-free process)
 - for all BGA, HTSSON..T and SSOP..T packages
 - for packages with a thickness ≥ 2.5 mm
 - for packages with a thickness < 2.5 mm and a volume ≥ 350 mm³ so called thick/large packages.
- below 240 °C (SnPb process) or below 260 °C (Pb-free process) for packages with a thickness < 2.5 mm and a volume < 350 mm³ so called small/thin packages.

Moisture sensitivity precautions, as indicated on packing, must be respected at all times.

16.3 Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.

- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27 mm, the footprint longitudinal axis is **preferred** to be parallel to the transport direction of the printed-circuit board;
 - smaller than 1.27 mm, the footprint longitudinal axis **must** be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

- For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time of the leads in the wave ranges from 3 to 4 seconds at 250 °C or 265 °C, depending on solder material applied, SnPb or Pb-free respectively.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

16.4 Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

16.5 Package related soldering information

Table 18: Suitability of surface mount IC packages for wave and reflow soldering methods

Package ^[1]	Soldering method	
	Wave	Reflow ^[2]
BGA, HTSSON..T ^[3] , LBGA, LFBGA, SQFP, SSOP..T ^[3] , TFBGA, USON, VFBGA	not suitable	suitable
DHVQFN, HBCC, HBGA, HLQFP, HSO, HSOP, HSQFP, HSSON, HTQFP, HTSSOP, HVQFN, HVSON, SMS	not suitable ^[4]	suitable
PLCC ^[5] , SO, SOJ	suitable	suitable
LQFP, QFP, TQFP	not recommended ^{[5][6]}	suitable
SSOP, TSSOP, VSO, VSSOP	not recommended ^[7]	suitable
CWQCCN..L ^[8] , PMFP ^[9] , WQCCN..L ^[8]	not suitable	not suitable

[1] For more detailed information on the BGA packages refer to the *(LF)BGA Application Note* (AN01026); order a copy from your Philips Semiconductors sales office.

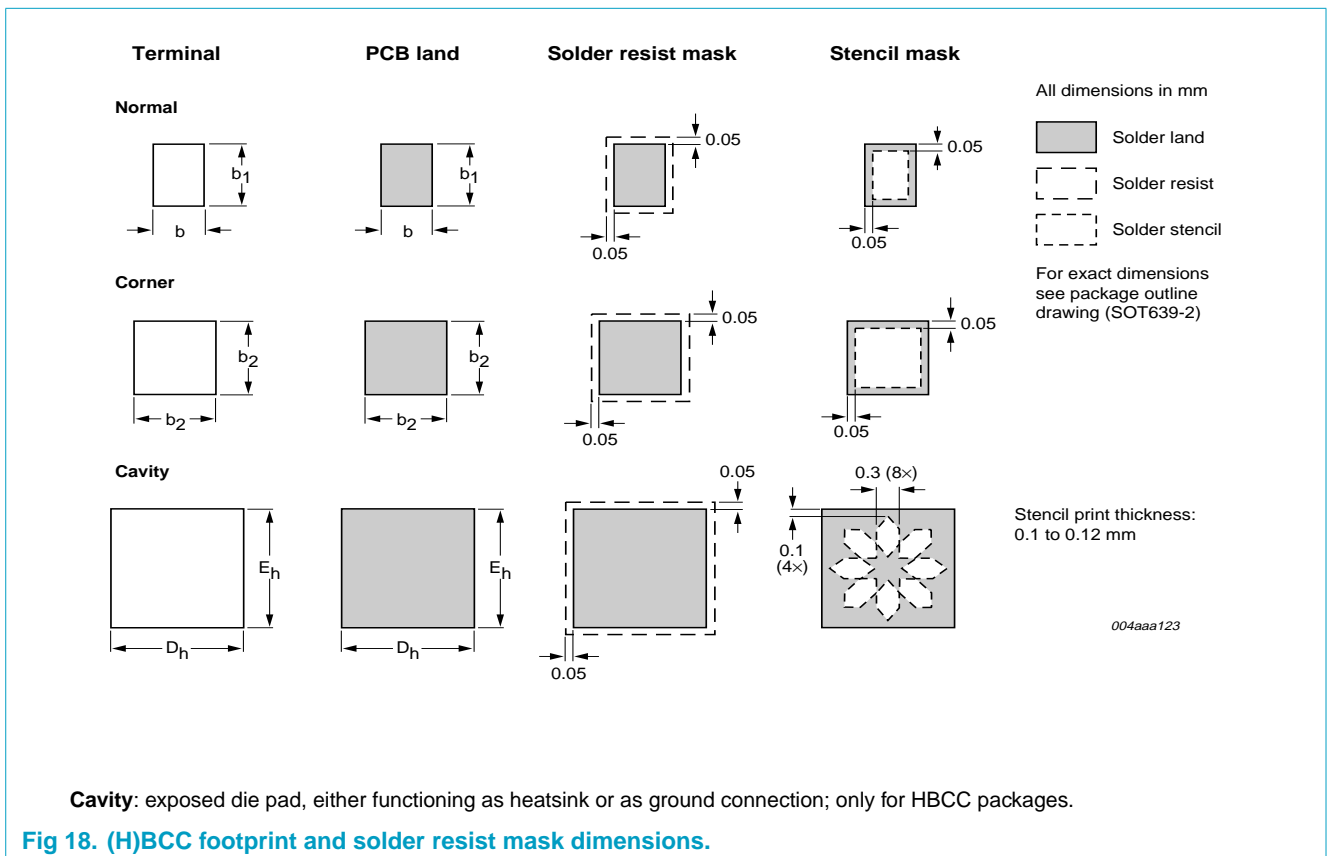
[2] All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the *Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods*.

- [3] These transparent plastic packages are extremely sensitive to reflow soldering conditions and must on no account be processed through more than one soldering cycle or subjected to infrared reflow soldering with peak temperature exceeding $217\text{ °C} \pm 10\text{ °C}$ measured in the atmosphere of the reflow oven. The package body peak temperature must be kept as low as possible.
- [4] These packages are not suitable for wave soldering. On versions with the heatsink on the bottom side, the solder cannot penetrate between the printed-circuit board and the heatsink. On versions with the heatsink on the top side, the solder might be deposited on the heatsink surface.
- [5] If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- [6] Wave soldering is suitable for LQFP, QFP and TQFP packages with a pitch (e) larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- [7] Wave soldering is suitable for SSOP, TSSOP, VSO and VSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.
- [8] Image sensor packages in principle should not be soldered. They are mounted in sockets or delivered pre-mounted on flex foil. However, the image sensor package can be mounted by the client on a flex foil by using a hot bar soldering process. The appropriate soldering profile can be provided on request.
- [9] Hot bar soldering or manual soldering is suitable for PMFP packages.

17. Additional soldering information

17.1 (H)BCC packages: footprint

The surface material of the terminals on the resin protrusion consists of a 4-layer metal structure (Au, Pd, Ni and Pd). The Au + Pd layer (0.1 µm min.) ensures solderability, the Ni layer (5 µm min.) prevents diffusion, and the Pd layer on top (0.5 µm min.) ensures effective wire bonding.



17.2 (H)BCC packages: reflow soldering profile

The conditions for reflow soldering of (H)BCC packages are as follows:

- **Preheating time:** minimum 90 s at $T = 145$ to 155 °C
- **Soldering time:** minimum 90 s (BCC) or minimum 100 s (HBCC) at $T > 183$ °C
- **Peak temperature:**
 - Ambient temperature: $T_{amb(max)} = 260$ °C
 - Device surface temperature: $T_{case(max)} = 255$ °C.

18. Revision history

Table 19: Revision history

Rev	Date	CPCN	Description
08	20040219	-	Product data (9397 750 11231); removed ISP1107 related information. Modifications: <ul style="list-style-type: none"> • Changed the data sheet title from ISP1105/1106/1107 to ISP1105/1106 and removed all information pertaining to ISP1107 • Changed USB 1.1 reference to USB 2.0; also added data transfer rates • Added HVQFN16 package details in Table 1, Section 6 and Section 14 • Figure 1: removed the first figure note • Table 3: added pad details • Table 11: updated • Table 15: removed Z_{DRV2}, and also table note 3 • Figure 8 and Figure 10: changed 1.65 V to 1.8 V.
07	20020329	-	Product data (9397 750 09529)
06	20011130	-	Product data; sixth version (9397 750 08872)
05	20010903	-	Product data; fifth version (9397 750 08681)
04	20010802	-	Preliminary data; fourth version (9397 750 08643)
03	20010704	-	Preliminary data; third version (9397 750 08515)
02	20010205	-	Objective specification; second version (9397 750 07879) ISP1107 stand-alone data sheet only.
01	20000223	-	Objective specification; initial version (9397 750 06899) ISP1107 stand-alone data sheet only.

19. Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2][3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

20. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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